

3-Channel Power Management IC For Portable Devices

GENERAL DESCRIPTION

The EMQ8931 is a high efficiency, 3-channel power management IC for portable devices application. It integrates a complete linear charger for single cell lithium-ion battery, a linear regulator and a high efficiency step-down DC/DC converter.

The linear charger (CH1) operates from 4.25V to 5.5V input voltage and up to 1A charging capability. It is thermal regulated and specifically designed to work within USB power specifications.

The linear regulator (CH2) features ultra-high power supply rejection ratio (75dB at 1kHz), low output voltage noise (30μ V), low dropout voltage (180mV), low quiescent current (110μ A) and fast transient response. It operates from 2.5V to 5.5V input voltage, up to 300mA loading capability and regulates adjustable output voltage from 1.2V to 5.0V.

The Synchronous Buck converter (CH3) operates from 2.5V to 5.5V input voltage, up to 600mA loading capability and regulate adjustable output voltage from 0.6V to V_{IN} . It features low quiescent current, 1.5MHz internal frequency operation.

The EMQ8931 is available in TSSOP-20FD package, It is RoHS (Pb-free).

FEATURES

Linear Charger

- * 4.25V to 5.5V Input Voltage
- * Programmable charge current up to 1A
- Thermal regulation maximizes charge rate without risk of overheating
- * Act as a LDO when battery is removed
- * Preset 4.2V charge voltage with ±1%

accuracy

- * Automatic recharge
- * Charge status indicator
- * C/10 charge termination
- * Battery reverse leakage current less than 1µA
- * 45µA shutdown supply current
- * Soft-start limits inrush current

Linear Regulator

- * 1.2V to 5.0V Output Voltage
- * 75dB Typical PSRR at 1kHz
- 30µV RMS Output Voltage Noise (10Hz to 100kHz)
- * 180mV Typical Dropout at 300mA

Synchronous Buck Converter

- * 0.6V to VIN Output Voltage
- * Up to 95% Efficiency
- * Low Dropout Operation: 100% Duty Cycle
- * No Schottky Diode Needed
- Shutdown Current < 1µA (CH1-CH3)
- Independent Enable PIN(CH1-CH3)
- Independent Input Voltage PIN(CH1-CH3)
- No External Compensation Network is needed
- Excellent Line and Load Transient Response(CH1-CH3)
- Over Current Protection
- Over Temperature Protection

APPLICATIONS

- Hand-held Instruments
- Portable information applications
- Wireless Networking
- GPS
- MP3/MP4/PMP Multi-media



Preliminary

EMQ8931

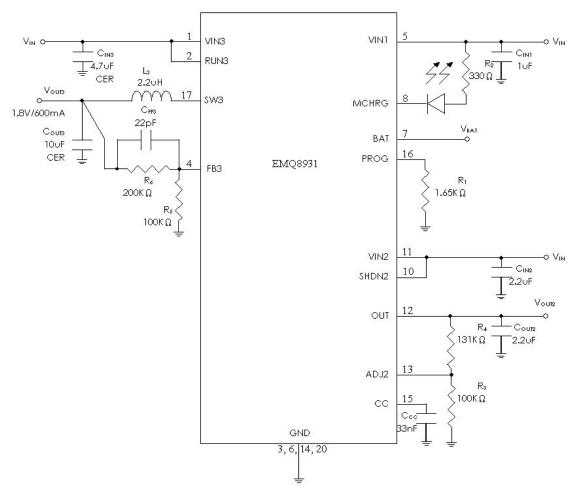
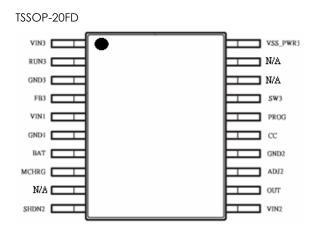


Figure 1. Typical Application

CONNECTION DIAGRAM



ORDER INFORMATION

EMQ8931-00QE20GRR

00	Adjustable output voltage			
QE20	TSSOP-20FD Package			
GRR	RoHS (Pb-free)			
	Commercial Grade Temperature			
	Rating: -40 to 85°C			
	Package in Tape & Reel			



MARKING & PACKING INFORMATION

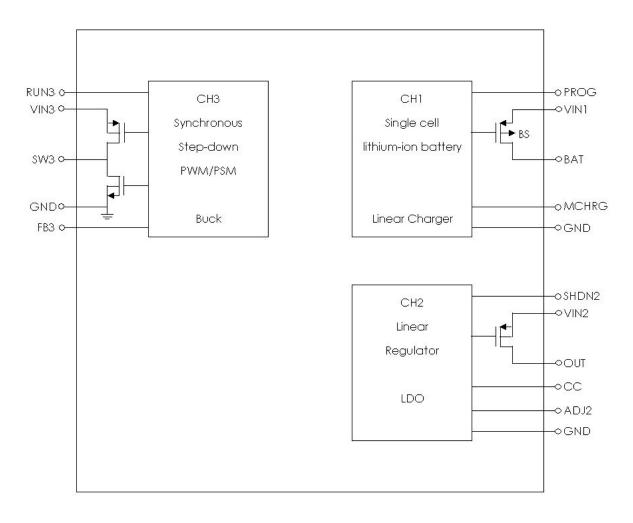
Package Type	Product ID	Package Marking	Transport Media
TSSOP-20FD	EMQ8931-00QE20GRR		2.5K units Tape & Reel

TERMINAL FUNCTIONS

TERMINAL		- 1/0	DECONIDION		
NAME	NO.	1/0	DESCRIPTION		
VIN3	1	Ι	CH3 Input Voltage.		
Run3	2	Ι	CH3 Enable Input.		
GND	3, 6, 14, 20	-	Ground.		
FB3	4	Ι	CH3 Voltage Feedback PIN.		
VIN1	5	Ι	CH1 Positive Input Supply Voltage.		
BAT	7	0	CH1 Charge Current Output and battery voltage feedback.		
MCHRG	8	Ι	CH1 Open-Drain Charge Status Output.		
N/A	9, 18, 19	-	No connection PIN.		
SHDN2	10	Ι	CH2 Enable Input.		
VIN2	11	Ι	CH2 Input Voltage.		
OUT	12	0	CH2 Output Voltage Feedback.		
ADJ2	13	Ι	CH2 Adjustable Negative Feedback Control.		
СС	15	Ι	CH2 Compensation Capacitor.		
PROG	16	Ι	CH1 Charge Current Program PIN, IBAT=(VPROG/RPROG)*960		
			The PROG pin must not be directly shorted to ground at any condition.		
SW3	17	0	CH3 Switch PIN. Must be connected to Inductor.		



FUNCTION BLOCK DIAGRAM





ABSOLUTE MAXIMUM RATINGS

Supply Input Voltage	-0.3V to 6.0V	ESD Susceptibility	TBD
(VIN, VIN2, VIN3)		Junction Temperature	150°C
BAT PIN Voltage	-0.3V to 6.0V	Thermal Resistance	
MCHRG PIN Voltage	-0.3V to 6.0V	θ_{JA} (TSSOP-20FD)	55°C/W
PROG PIN Voltage	-0.3V to 6.0V	Operating Ratings	
SW3 Switch PIN Voltage	-0.3V to (VIN3+0.3V)	Temperature Range	$\text{-40°C} \ \leq \ T_A \leq \ 85^{\circ}\text{C}$
Other I/O PIN Voltage	-0.3V to (VIN+0.3V)	VIN Supply Voltage	$4.25V~\leq~V_{\text{DD}}\leq~5.5V$
Storage Temperature	-65°C to +150°C	Supply Voltage	$2.5V~\leq~V_{\text{DD}}\leq~5.5V$
Power Dissipation	2.2W	(VIN2, VIN3)	

ELECTRICAL CHARACTERISTICS

Apply for V_{IN} =5.0V, V_{IN2} = V_{OUT2} +1V (Note 6), V_{SHDN2} = V_{IN2} , C_{IN2} = C_{OUT2} = 2.2 μ F, C_{CC2} = 33nF, V_{IN3} = 3.6V and T_A = 25°C (unless otherwise noted), Boldface limits apply for the operating temperature extremes: -40°C and 85°C.

Symbol	Parameter	Conditions	EMQ8931			Units	
Symbol	Parameter	Conditions	Min	Тур	Max	UTIILS	
CH1				-			
VIN	Input voltage		4.25		5.5	V	
		Charge Mode, R _{PROG} =10K (Note 4)		260		μA	
	Input Supply Current	Standby Mode (Charge Terminated)		106			
lcc	input supply Current	Shutdown Mode (R _{PROG} Not Connected, V _{IN} <v<sub>BAT or V_{IN} <v<sub>UV)</v<sub></v<sub>		45			
Vfloat	Regulated Output (Float) Voltage	$0^{o}C ~\leq~ T_A ~\leq~ 85^{o}C$	4.158	4.2	4.242	V	
	BAT Pin Current	R _{PROG} =2K, Current Mode		480		mA	
		Standby Mode, V _{BAT} =4.2V	-1	0	1	μΑ	
IBAT		Shutdown Mode (R _{PROG} Not Connected)	-1	0	1		
		Sleep Mode, V _{IN} =0V	-1	0	1		
Itrickle	Trickle Charge Current	VBAT <vtrickle, rprog="2K</td"><td></td><td>50</td><td></td><td>mA</td></vtrickle,>		50		mA	
VTRICKLE	Trickle Charge Threshold Voltage	R _{PROG} =10K, V _{BAT} Rising		2.9		V	
V _{TRHYS}	Trickle Charge Hysteresis Voltage	R _{PROG} =10K		210		mV	
Vuv	V _{IN} Under voltage Lockout Threshold	From VIN Low to High		3.0		V	
Vuvhys	V _{IN} Under voltage Lockout Hysteresis			180		mV	
Vasd	VIN-VBAT Lockout Threshold	$V_{\ensuremath{IN}}$ from Low to High		80		mV	



	Voltage	$V_{\ensuremath{IN}}$ from High to Low		30		mV
I _{term}	C/10 Termination Current Threshold	R _{PROG} =10K		0.1		mA/mA
V _{PROG}	PROG Pin Voltage	R _{PROG} =10K, Current Mode		1.0		V
Існдв	CHGB Pin Weak Pull-Down Current	V _{CHGB} =5V		24		μΑ
VCHGB	CHGB Pin Output Low Voltage	I _{CHGB} =5mA		0.23		V
Vrechrg	Recharge Battery Threshold Voltage	Vfloat-Vrechrg		160		mV
Tilm	Junction Temperature in Constant Temperature Mode			120		°C
Ron	Power FET "ON" Resistance			560		mΩ
Tss	Soft-Start Time	IBAT=0 to IBAT=960V/RPROG		100		μs
Trecharge	Recharge Comparator Filter Time	V _{BAT} High to Low		2.4		ms
Tterm	Termination Comparator Filter Time	IBAT Falling Below ICHG/10		1.1		ms
IPROG	PROG Pin Pull-up Current			0.4		μΑ
CH2 (note	8)			r	1	1
V _{IN2}	Input Voltage		2.5		5.5	V
ΔV_{OTL2}	Output Voltage Tolerance	$100\mu A \le I_{OUT2} \le 300 \text{mA}$ $V_{OUT2 (NOM)} + 0.5 \text{V} \le \text{VIN2} \le$ 5.5 V (Note 5) $ADJ2=V_{OUT2}$	-2		+2	% of
			-3		+3	Vout (NOM)
V _{OUT2}	Output Adjust Range		1.20		5.0	V
Iout2	Maximum Output Current	Average DC Current Rating	300			mA
ILIMIT2	Output Current Limit		330	600		mA
	Supply Current	I _{OUT2} = 0mA		100		
Iq2		Iout2 = 300mA		130		μA
	Shutdown Supply Current	V _{OUT2} = 0V, SHDN2 = GND		0.001	1	
V _{DO2}	Dropout Voltage	Iout2 = 50mA		31		
		I _{OUT2} = 150mA		94		mV
	(Note 5)	I _{OUT2} = 300mA		180		1
ΔV_{OU2T}	Line Regulation	$I_{OUT2} = 1 \text{mA}, (V_{OUT2} + 0.5 \text{V}) \le V_{IN2} \le 5.5 \text{V}$ (Note 6)	-0.1	0.02	0.1	%/V



	Load Regulation	100µA ≤ I _{OUT2} ≤ 600mA		0.001		%/mA
e _{n2}	Output Voltage Noise	I _{OUT2} = 10mA, 10Hz ≤ f ≤ 100kHz		30		μV _{RMS}
V _{SHDN2}	SHDN2 Input Threshold	V_{IH} , $(V_{OUT} + 0.5V) \le V_{IN} \le 5.5V$ (Note 8)	1.2			V
V SHDINZ		V_{IL} (V_{OUT} + 0.5V) $\leq V_{IN} \leq 5.5V$ (Note 8)			0.4	
Ishdn2	SHDN2 Input Bias Current	SHDN2 = GND or VIN		0.1	100	nA
I _{ADJ2}	ADJ2 Input Leakage	ADJ2=1.3V (Note 7)		0.1	3	nA
Tsd	Thermal Shutdown Temperature	(Note 8)		165		°C
Tsd_hyst	Thermal Shutdown Hysteresis			25		°C
T _{ON2}	Start-Up Time	C _{OUT2} = 10µF, V _{OUT2} at 90% of Final Value		50		μs
CH3 (Note	8)					
Ivfb3	Feedback Current				±30	nA
V _{FB3}	Regulated Feedback Voltage	T _A = 25°C	0.588	0.600	0.612	V
•185		–40°C ≤ T _A ≤ 85°C	0.585	0.600	0.615	
ΔV_{FB3}	Reference Voltage Line Regulation	V _{IN3} = 2.5V to 5.5V			0.4	%/V
ΔV_{OVL3}	Output Over-voltage Lockout	$\Delta V_{OVL3} = V_{OVL3} - V_{FB3}$	20	50	80	mV
	Output Voltage Line Regulation	V _{IN3} = 2.5V to 5.5V			0.4	%/V
ΔV_{OUT3}	Output Voltage Load Regulation			0.5		%
Іркз	Peak Inductor Current	V _{IN3} = 3V, V _{FB3} = 0.5V or V _{OUT3} = 90%, Duty Cycle < 35%		1.0		A
	Quiescent Current (Note 9)	$V_{FB3} = 0.5V \text{ or } V_{OUT3} = 90\%$		200	340	μA
IQ3	Shutdown	V _{EN3} = 0V, V _{IN3} = 4.2V		0.1	1	μA
fosc3	Oscillator Frequency	$V_{FB3} = 0.6V \text{ or } V_{OUT3} = 100\%$	1.2	1.5	1.8	MHz
105C3		$V_{FB3} = 0V \text{ or } V_{OUT3} = 0V$		290		kHz
R _{PFET3}	R _{DS(ON)} of PMOS	I _{SW3} = 100mA		0.48	0.58	Ω
R _{NFET3}	R _{DS(ON)} of NMOS	I _{SW3} = -100mA		0.47	0.57	Ω
I _{SW3}	SW3 Leakage	$V_{SW3} = 0V$, $V_{SW3} = 0V$ or $5V$, $V_{IN3} = 5V$			±1	μA
V_{EN3}	RUN3 Threshold		0.5		1.3	V
I _{EN3}	RUN3 Leakage Current				±1	μA



Note 1: Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.

Note 2: All voltages are with respect to the potential at the ground pin.

Note 3: Maximum Power dissipation for the device is calculated using the following equations:

$$P_D = \frac{T_J(MAX) - T_A}{\theta_{JA}}$$

where TJ(MAX) is the maximum junction temperature, TA is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

- Note 4: CH1 Supply current includes PROG pin current (approximately 100µA) but does not include any current delivered to the battery through the BAT pin (approximately 96mA).
- Note 5: CH2 does not apply to input voltages below 2.5V since this is the minimum input operating voltage.
- Note 6: CH2 Dropout voltage is measured by reducing V_{IN} until V_{OUT} drops 100mV from its nominal value at V_{IN} - $V_{OUT} = 0.5V$. Dropout voltage does not apply to the regulator versions with V_{OUT} less than 2.5V.
- Note 7: CH2 The ADJ2 pin is disconnected internally for the preset versions.

Note 8: CH2 and CH3 build-in internal over-temperature protection to prevent over-load condition.

Note 9: Dynamic quiescent current is higher due to the gate charge delivered at the switching frequency.

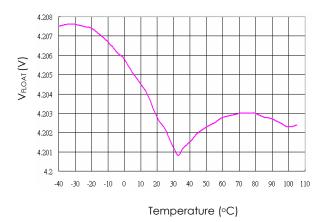


TYPICAL PERFORMANCE CHARACTERISTICS

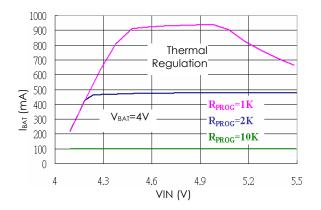
 $V_{\text{IN1}}=5.0V, V_{\text{IN2}}=V_{\text{OUT2}(\text{NOM})}+1V, C_{\text{IN2}}=C_{\text{OUT2}}=2.2\mu\text{F}, C_{\text{CC}}=33\text{nF}, V_{\text{SHDN2}}=V_{\text{IN2}}, V_{\text{EN3}}=V_{\text{IN3}}, C_{\text{IN3}}=4.7\mu\text{F}, L_3=2.2\mu\text{H}, C_{\text{OUT3}}=4.7\mu\text{F}, L_4=25^{\circ}\text{C}, unless otherwise specified$

CH1 Regulated Output (Float) Voltage vs Temperature

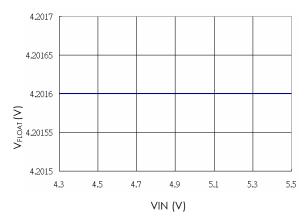
CH1 Charge Current vs Battery Voltage

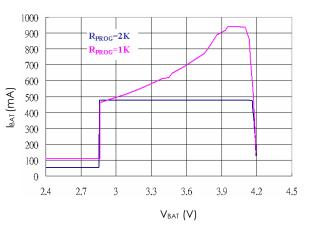




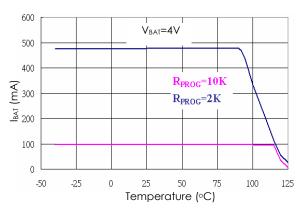


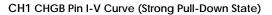
CH1 Regulated Output (Float) Voltage vs Supply Voltage

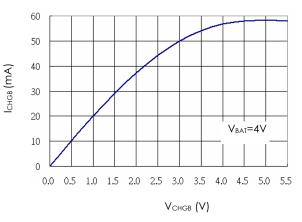




CH1 Charge Current vs Ambient Temperature



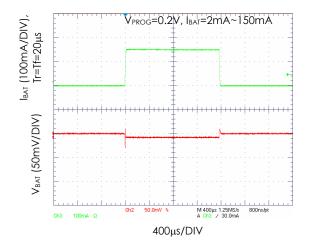


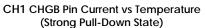


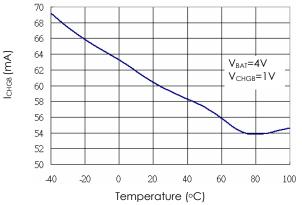


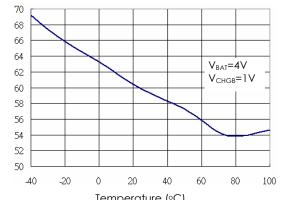
CH1 Load Transient (Battery Removed)

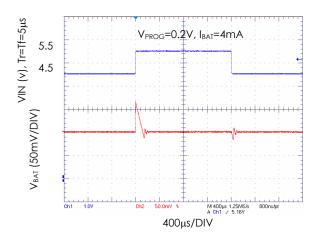
CH1 Line Transient (Battery Removed)



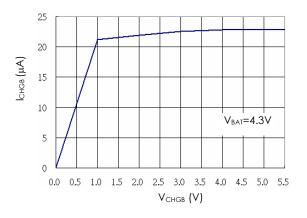


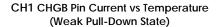


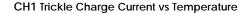


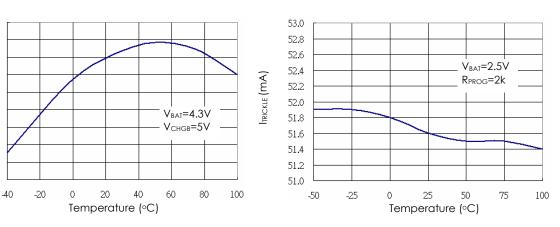


CH1 CHGB Pin I-V Curve (Weak Pull-Down State)









Elite MicroPower Inc. reserves the right to make changes to improve reliability or manufacturability without notice, and customers are advised to obtain the latest version of relevant information prior to placing orders.

22.8

22.6

22.4

22.2

22.0

21.8

21.6

21.4

21.2

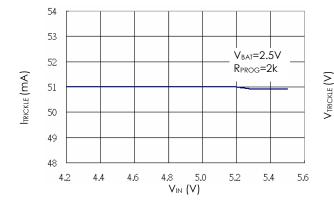
21.0

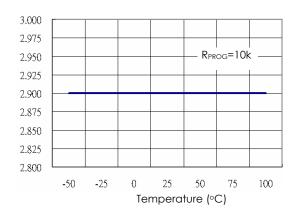
ICHGB (µA)



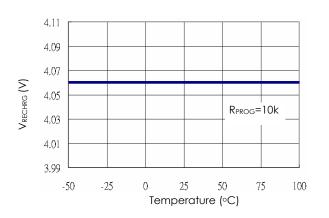
CH1 Trickle Charge Current vs Supply Voltage

CH1 Trickle Charge Threshold vs Temperature

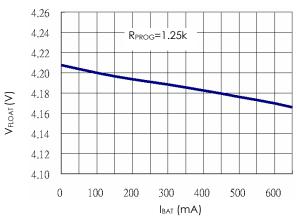


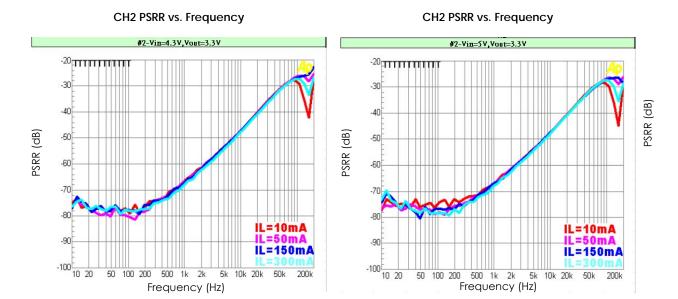


CH1 Recharge Voltage Threshold vs Temperature

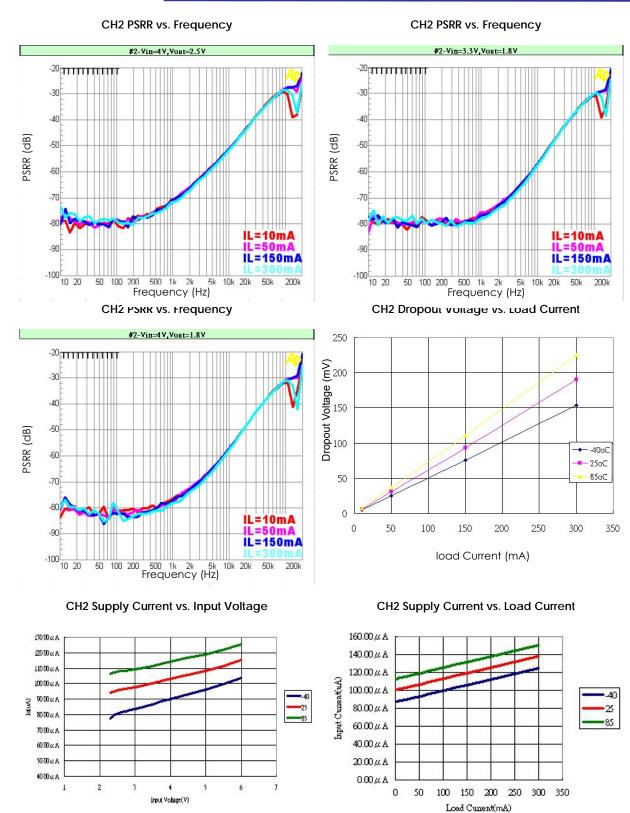


CH1 Regulated Output (Float) Voltage vs Charge Current



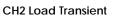


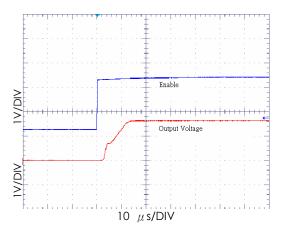




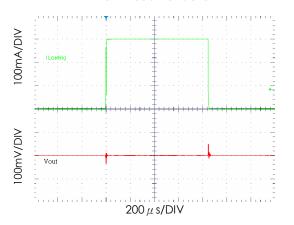


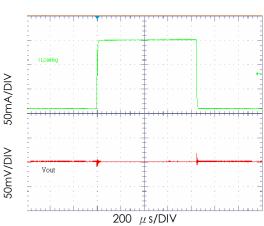
CH2 Enable Response



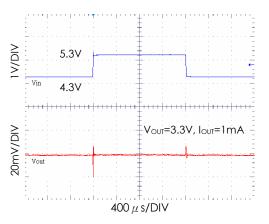


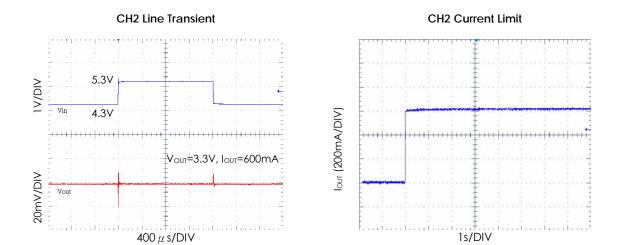
CH2 Load Transient





CH2 Line Transient

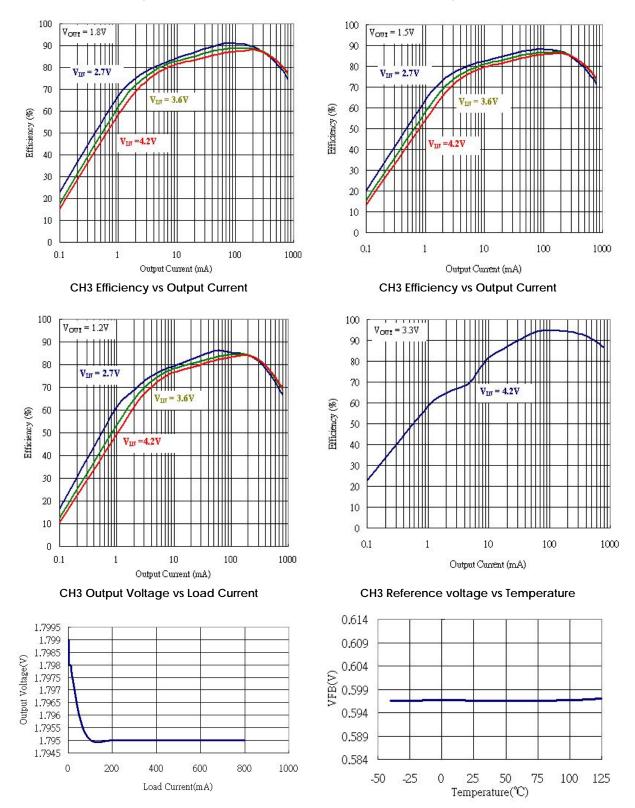






CH3 Efficiency vs Output Current

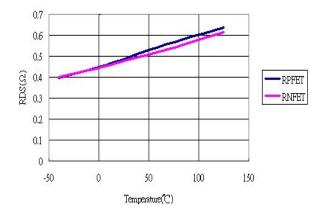
CH3 Efficiency vs Output Current

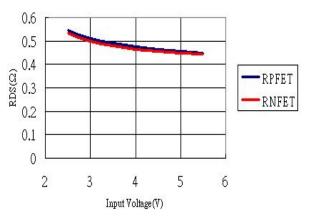


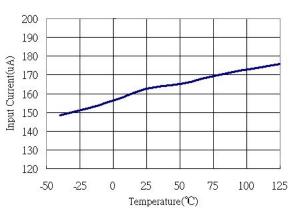


CH3 R_{DS(ON)} vs Temperature



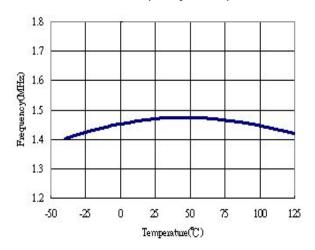




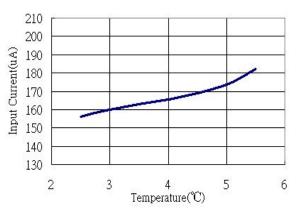


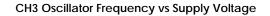
CH3 Dynamic Supply Current vs Temperature

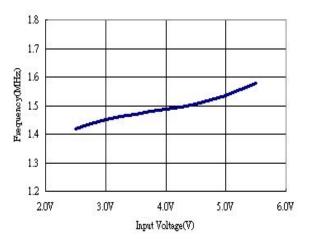
CH3 Oscillator Frequency vs Temperature



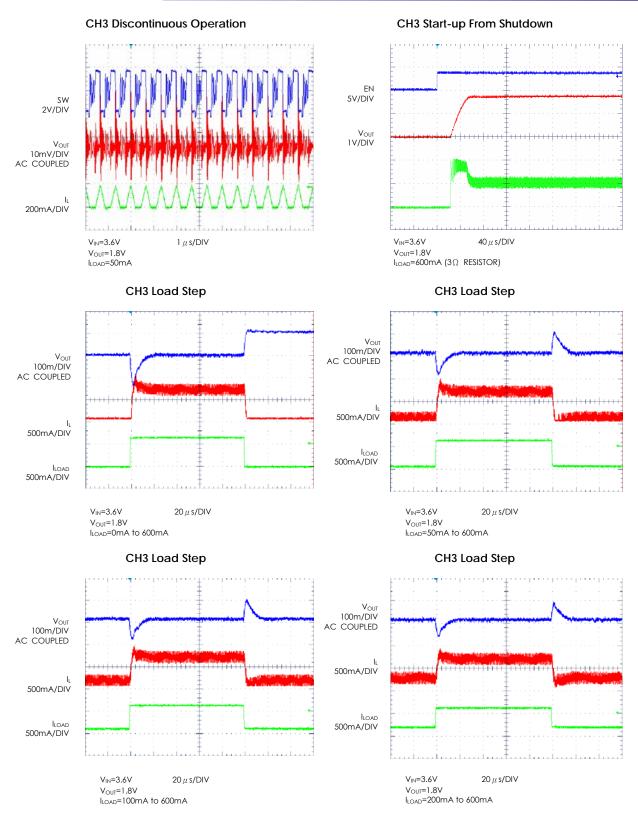
CH3 Dynamic Supply Current vs Supply Voltage













Preliminary

Application Information

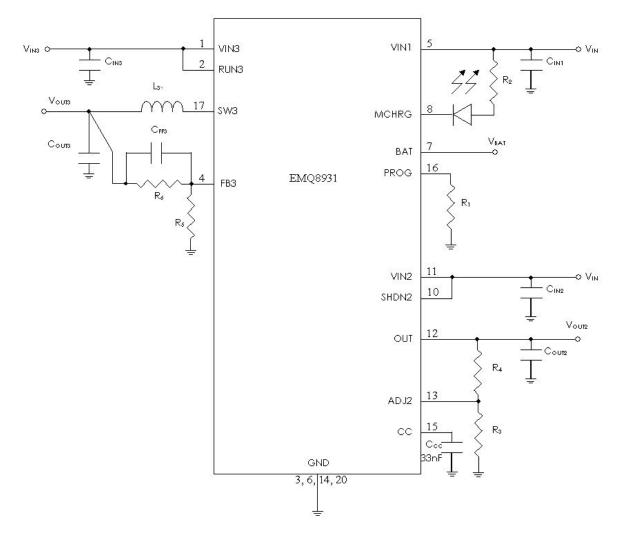


Figure 2. Typical EM8931 Application Circuit That Supports One lithium-ion Linear Charger and Two Adjustable Output Voltage



Application Information

The EMQ8931 is a high efficiency, 3-channel power management IC for portable devices application.

The Three channels are listed as following : CH1 : Linear charger for single cell lithium-ion battery CH2 : High PSRR, low noise, low dropout 300mA LDO CH3 : 600mA Synchronous Buck converter CH2/3 are Vout adjustable

CH1 Linear Charger

CH1: The Linear Charger is a complete linear charger for single cell lithium-ion battery that is specifically designed to work within USB power specifications.

No external sense resistor and blocking diode are required. Charging current can be programmed externally with a single resistor. The built-in thermal regulation facilitates charging with maximum power without risk of overheating.

The charger always preconditions the battery with 1/10 of the programmed charge current at the beginning of a charge cycle, until 40 s after it verifies that the battery can be fast-charged. The charger automatically terminates the charge cycle when the charge current drops to 1/10th the programmed value after the final float voltage is reached.

The charger can also be used as a LDO when battery is removed. Other features include reverse current protection, shutdown mode, charge current monitor, under voltage lockout, automatic recharge and status indicator.

CH1 Programming Charging Current

The Charging current (I_{BAT}) can be programmed up to 1.0A by equation (1).

 $I_{BAT} = (V_{PROG}/R_{PROG})*960....(1)$

CH2: High PSRR, low noise, low dropout 300mA LDO

The LDO adopts the classical regulator topology in which negative feedback control is used to perform

the desired voltage regulating function. The negative feedback is formed by using feedback resistors (R3, R4) to sample the output voltage (Vour2) for the non-inverting input of the error amplifier, whose inverting input is set to the bandgap reference voltage. By virtue of its high open-loop gain, the error amplifier operates to ensure that the sampled output feedback voltage at its non-inverting input is virtually equal to the preset bandgap reference voltage.

The error amplifier compares the voltage difference at its inputs and produces an appropriate driving voltage to the P-channel MOS pass transistor to control the amount of current reaching the output. If there are changes in the output voltage due to load changes, the feedback resistors register such changes to the non-inverting input of the error amplifier. The error amplifier then adjusts its driving voltage to maintain virtual short between its two input nodes under all loading conditions. In a nutshell, the regulation of the output voltage is achieved as a direct result of the error amplifier keeping its input voltages equal. This negative feedback control topology is further augmented by the shutdown, the temperature protection and current protection circuitry.

CH2 Output Voltage Control

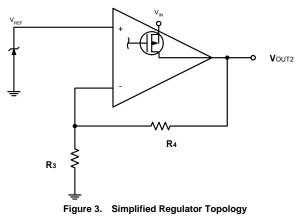
The LDO allows direct user control of the output voltage in accordance with the amount of negative feedback present. To see the explicit relationship between the output voltage and the negative feedback, it is convenient to conceptualize the LDO as an ideal non-inverting operational amplifier with a fixed DC reference voltage V_{REF2} at its non-inverting input. Such a conceptual representation of the LDO in closed-loop configuration is shown in Figure 4. This ideal op amp features an ultra-high input resistance such that its inverting input voltage is virtually fixed at V_{REF2}. The output voltage is therefore given by:



 $V_{OUT2} = V_{REF2} \left[\frac{R_4}{R_3} + 1 \right] \dots (2)$

This equation can be rewritten in the following form to facilitate the determination of the resistor values for a chosen output voltage:

Set R3 equal to $100k \Omega$ to optimize for overall accuracy, power supply rejection, noise, and power consumption.



CH2 Output Capacitor

The LDO is specially designed for use with ceramic output capacitors of as low as 2.2µF to take advantage of the savings in cost and space as well as the superior filtering of high frequency noise. Capacitors of higher value or other types may be used, but it is important to make sure its equivalent series resistance (ESR) be restricted to less than 0.5Ω . The use of larger capacitors with smaller ESR values is desirable for applications involving large and fast input or output transients, as well as for situations where the application systems are not physically located immediately adjacent to the battery power source. Typical ceramic capacitors suitable for use with the LDO are X5R and X7R. The X5R and the X7R capacitors are able to maintain their capacitance values to within ±20% and ±10%, respectively, as the temperature increases.

CH2 No-Load Stability

The LDO is capable of stable operation during no-load conditions, a mandatory feature for some applications such as CMOS RAM keep-alive operations.

CH2 Input Capacitor

A minimum input capacitance of 1µF is required for the LDO. The capacitor value may be increased without limit. Improper workbench set-ups may have adverse effects on the normal operation of the regulator. A case in point is the instability that may result from long supply lead inductance coupling to the output through the gate capacitance of the pass transistor. This will establish a pseudo LCR network, and is likely to happen under high current conditions or near dropout. A 10µF tantalum input capacitor will dampen the parasitic LCR action thanks to its high ESR. However, cautions should be exercised to avoid regulator short-circuit damage when tantalum capacitors are used, for they are prone to fail in short-circuit operating conditions.

■ CH2 Compensation (Noise Bypass) Capacitor

Substantial reduction in the output voltage noise of the LDO is accomplished through the connection of the noise bypass capacitor C_{CC} (33nF optimum) between CC pin and the ground. Because CC pin connects directly to the high impedance output of the bandgap reference circuit, the level of the DC leakage currents in the Ccc capacitors used will adversely reduce the regulator output voltage. This sets the DC leakage level as the key selection criterion of the C_{CC} capacitor types for use with the LDO. NPO and COG ceramic capacitors typically offer very low leakage. Although the use of the C_{CC} capacitors does not affect the transient response, it does affect the turn-on time of the regulator. Tradeoff exists between output noise level and turn-on time when selecting this capacitor value.



CH2 Power Dissipation and Thermal Shutdown

Thermal overload results from excessive power dissipation that causes the IC junction temperature to increase beyond a safe operating level. The LDO relies on dedicated thermal shutdown circuitry to limit its total power dissipation. An IC junction

temperature T_J exceeding 165°C will trigger the thermal shutdown logic, turning off the P-channel MOS pass transistor. The pass transistor turns on again after the junction cools off by about 30°C. When continuous thermal overload conditions persist, this thermal shutdown action then results in a pulsed waveform at the output of the regulator. The concept of thermal resistance θ_{JA} (°C/W) is often used to describe an IC junction's relative readiness in allowing its thermal energy to dissipate to its ambient air. An IC junction with a low thermal resistance is preferred because it is relatively effective in dissipating its thermal energy to its ambient, thus resulting in a relatively low and desirable junction temperature. The relationship between θ_{JA} and T_J is as follows:

 $T_{J} = \theta_{JA} (PD) + T_{A}$ (4)

 T_A is the ambient temperature, and P_D is the power generated by the IC and can be written as:

 $P_{D} = I_{OUT} (V_{IN} - V_{OUT})$ (5)

As the above equations show, it is desirable to work with ICs whose θ_{JA} values are small such that T_J does not increase strongly with P_D. To avoid thermal overloading the LDO, refrain from exceeding the absolute maximum junction temperature rating of 150°C under continuous operating conditions. Overstressing the regulator with high loading currents and elevated input-to-output differential voltages can increase the IC die temperature significantly.

CH2 Shutdown

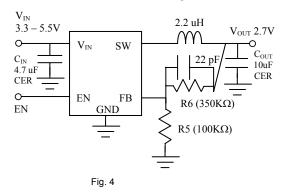
CH2 enters the sleep mode when the SHDN2 pin is low. When this occurs, the pass transistor, the error amplifier, and the biasing circuits, including the bandgap reference, are turned off, thus reducing the supply current to typically 1nA. Such a low supply current makes the LDO best suited for battery-powered applications. The maximum guaranteed voltage at the SHDN2 pin for the sleep mode to take effect is 0.4V. A minimum guaranteed voltage of 1.2V at the SHDN2 pin would activate the LDO. Direct connection of the SHDN2 pin to the V_{IN2} to keep the regulator on is allowed for the LDO. In this case, the SHDN2 pin must not exceed the supply voltage V_{IN2}.

Fast Start-Up

Fast start-up time is important for overall system efficiency improvement. The LDO assures fast start-up speed when using the optional noise bypass capacitor (C_{CC}). To shorten start-up time, the LDO internally supplies a 500µA current to charge up the capacitor until it reaches about 90% of its final value.

CH3: 600mA Synchronous Buck converters

The typical application circuit of the current mode DC/DC converter is shown in Fig.4.



CH3 Inductor Selection

Basically, inductor ripple current and core saturation are two factors considered to decide the Inductor



$$\Delta I_{L} = \frac{1}{f \cdot L} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right).....(6)$$

The Eq. 6 shows the inductor ripple current is a function of frequency, inductance, VI_{N3} (V_{IN3}) and V_{OUT} (V_{OUT3}). It is recommended to set ripple current to 40% of max. load current. A low ESR inductor is preferred.

■ CH3 C_{IN} and C_{OUT} Selection

A low ESR input capacitor can prevent large voltage transients at VI_N . The RMS current of input capacitor is required larger than I_{RMS} calculated by:

ESR is an important parameter to select Cout (Couts). The output ripple $\triangle V_{OUT}$ ($\triangle V_{OUT3}$) is determined by:

$$\Delta V_{OUT} \cong \Delta I_{L} \left(ESR + \frac{1}{8 \cdot f \cdot C_{OUT}} \right) \dots \dots \dots (8)$$

Higher values, lower cost ceramic capacitors are now available in smaller sizes. These ceramic capacitors have high ripple currents, high voltage ratings and low ESR that make them ideal for switching regulator applications. Optimize very low output ripple and small circuit size is doable from Cour selection since Cour does not affect the internal control loop stability. It is recommended to use the X5R or X7R which have the best temperature and voltage characteristics of all the ceramics for a given value and size.

CH3 Output Voltage

The output voltage can be determined by following equation:

$$V_{OUT} = 0.6 V \left(1 + \frac{R_6}{R_5} \right)$$
.....(9)

CH3 Thermal Considerations

Although thermal shutdown is build-in in the step-down DC/DC converter that protects the device from thermal damage, the total power

dissipation that the converter can sustain should be base on the package thermal capability. The formula to ensure the safe operation is shown in Note 3.

To avoid the DC/DC converter from exceeding the maximum junction temperature, the user will need to do some thermal analysis.

CH3 Guidelines for PCB Layout

To ensure proper operation of the DC/DC converter , please note the following PCB layout guidelines:

1. The GND trace, the SW (SW3) trace and the V_{IN} trace should be kept short, direct and wide.

2. V_{FB} (FB3) pin must be connected directly to the feedback resistors. Resistive divider R_5/R_6 must be connected and parallel to the output capacitor $C_{OUT}.$

3. The Input capacitor C_{IN} must be connected to pin V_{IN} as closely as possible.

4. Keep SW node away from the sensitive V_{FB} node since this node is with high frequency and voltage swing.

5. Keep the (–) plates of $C_{\ensuremath{\mathsf{IN}}}$ and $C_{\ensuremath{\mathsf{OUT}}}$ as close as possible.

CH3 Design Example

Assume the Step-down DC/DC converter is used in a single lithium-ion battery-powered application. The V_{IN} range will be about 2.7V to 4.2V. Output voltage is 1.8V.

With this information we can calculate L using equation:

Substituting $V_{OUT} = 1.8V$, $V_{IN} = 4.2V$, $I_L = 240$ mA and f = 1.5MHz in eq. 10 gives:



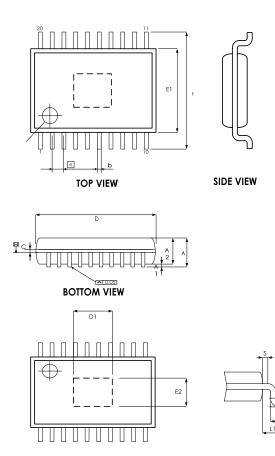
$$L = \frac{1.8V}{1.5MHz \cdot 240mA} \left(1 - \frac{1.8V}{4.2V} \right) = 2.86\mu H \dots (11)$$

A 2.2 μ H inductor could be chose with this application.

A greater inductor with less equivalent series resistance makes best efficiency. C_{IN} will require an RMS current rating of at least $I_{LOAD(MAX)}/2$ and low ESR. In most cases, a ceramic capacitor will satisfy this requirement.



TSSOP-20FD OUTLINE DIMENSION



SYMBOLS	MIN	NOM	MAX		
А	-	-	1.20		
Al	0.05	-	0.15		
a2	0.80	0.90	1.05		
b	0.19	-	0.30		
С	0.09	-	0.20		
D	6.40	6.50	6.60		
E1	4.30 4.40		4.50		
E	6.40 BSC				
е		0.65 BSC			
L1	1.00 BSC				
L	0.50	0.60	0.75		
S	0.20	-	-		
θ	0°	8°			
	•		Unit · mm		

Unit : mm

0.25





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